TRANSISTOR (PNP) **Plastic-Encapsulate Transistor**

FEATURES

Power dissipation

P_{CM} : 0.15W (Tamb=25°C)

Collector current

I_{CM} : -0.5A

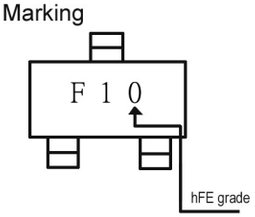
Collector-base Voltage

$V_{(BR)CBO}$: -35V

Operating and storage junction temperature range

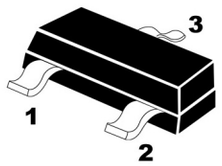
T_J, T_{stg} : -55°C to +150°C

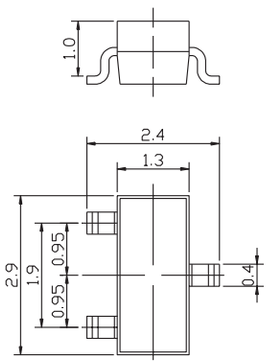
Marking



SOT-23

1. BASE
2. EMITTER
3. COLLECTOR





Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100 μA, I_E=0			-35	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-0.1mA, I_B=0			-30	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100 μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-35V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	70		240	
	$h_{FE(2)}$	V_{CE}=-6V, I_C=-400mA	25			
Collector-emitter saturation voltage	V_{CEsat}	I_C=-100mA, I_B=-10mA		-0.1	-0.25	V

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240

RoHS Pb-free TIP Semiconductor